REMARKS

This Supplemental Reply incorporates certain claim amendments and adds several new claims. The non-elected claims are being retained at the present time. Upon entry of this Supplemental Reply, claims 1-19, 21-59, and 61-92 will be present this application.

Claims 17-19, 21, 22, 58, 59, 66, 73-76 and 88-92 define the invention identified by the Examiner as invention II.

Respectfully submitted,

November 13, 2002

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In each claim appearing below, deletions are bracketed and additions are underlined.

17. (Amended) A layer structure usable in manufacturing an integrated circuit made by a process comprising:

providing a patterned substrate,

supplying an electrolyte solution out of which a conductive material can be plated, under an applied potential, over a surface of said patterned substrate,

applying a potential so as to deposit a planar film of said conductive material out of the electrolyte solution and over said surface of said patterned substrate [and polishing the film of said conductive material],

removing said conductive material from field regions of said patterned substrate while leaving deposits of said conductive material in features defined in said patterned substrate, and

electrically isolating said deposits of said conductive material.

18. (Amended) The layer structure of claim 17, wherein the [field regions] steps of providing, supplying, applying and removing are [regions of an insulator layer forming part of said patterned substrate] performed in the same apparatus.

19. (Amended) The layer structure of claim [17] 18, wherein at least one additional operation of depositing conductive material has been performed after removing said conductive material and before electrically isolating said deposits.

21. (Amended) The layer structure of claim 17, wherein said patterned substrate [included] includes an insulator layer and a barrier layer overlying said insulator layer, wherein said field regions are defined on said insulator

layer, and wherein said deposits of said conductive material have been electrically isolated by removal of said barrier layer from said field regions.

58. (Amended) A conductive material structure usable in manufacturing an integrated circuit made by a process comprising:

providing a substrate, wherein the surface of the substrate includes a top portion and cavity portions;

supplying an electrolyte solution out of which a conductive material can be plated, under an applied potential, over the surface of the substrate;

applying a potential so as to deposit a planar film of said conductive material out of the electrolyte solution and on the surface of the substrate [and polishing the film of said conductive material]; and

removing the conductive material from the top portion of the substrate while leaving deposits of the conductive material in the cavities.

59. (Amended) The conductive material of claim [58] 91, wherein at least one additional operation of depositing conductive material has been performed after removing the conductive material.